

NOT RECOMMENDED FOR NEW DESIGN **USE FZT688B**

DNLS412E



LOW VCE(SAT) NPN SURFACE MOUNT TRANSISTOR

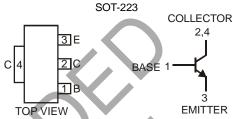
Features

- **Epitaxial Planar Die Construction**
- Low Collector-Emitter Saturation Resistance $R_{CE(SAT)} = 57.5 \text{m}\Omega$ at 4A
- High DC Current Gain hFE > 400 at IC = 3A
- Complementary PNP Type Available (DPLS315E)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.112 grams (approximate)





Schematic and Pin Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	12	V
Collector-Emitter Voltage	Vceo	12	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	Ic	4	A
Peak Pulse Current	I _{CM}	10	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation @T _A = 25°C (Note 3)	PD	1	W
Thermal Resistance, Junction to Ambient Air (Note 3) @T _A = 25°C	$R_{ heta JA}$	125	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- No purposefully added lead.
- Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

 Device mounted on FR-4 PCB, pad layout as shown on page 4 or in Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Off Characteristics						
Collector-Base Breakdown Voltage	V _{(BR)CBO}	12	_	_	V	$I_C = 100 \mu A, I_E = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	12	_	_	V	$I_C = 10 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5			V	$I_E = 100 \mu A, I_C = 0$
Collector Cutoff Current	I _{CBO}	_		100	nA	$V_{CB} = 10V, I_{E} = 0$
Emitter Cutoff Current	I _{EBO}	_		100	nA	$V_{EB} = 4V$, $I_C = 0$
On Characteristics (Note 4)						
		_	0.02	0.04		$I_C = 0.1A, I_B = 1mA$
		_	0.03	0.06		$I_C = 0.1A$, $I_B = 0.5mA$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	0.06	0.18	V	$I_C = 1A$, $I_B = 50mA$
		_	0.20	0.35		$I_C = 3A$, $I_B = 20mA$
		_	0.23	0.40		$I_C = 4A$, $I_B = 50mA$
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_		1.1	>	$I_C = 3A$, $I_B = 20mA$
Base-Emitter Turn-On Voltage	V _{BE(ON)}	_		1.0	V	$V_{CE} = 2V$, $I_C = 3A$
		500	_	_		$V_{CE} = 2V, I_{C} = 0.1A$
DC Current Gain	h_{FE}	400	_		-	$V_{CE} = 2V$, $I_C = 3A$
		100		_		$V_{CE} = 2V$, $I_C = 10A$
AC Characteristics						
Transition Frequency	f⊤	150	-		MHz	$V_{CE} = 5V, I_{C} = 50mA, f = 50MHz$
Input Capacitance	C _{ibo}		240		pF	$V_{EB} = 0.5V, f = 1MHz$
Output Capacitance	C _{obo}	_	35		pF	$V_{CB} = 10V, f = 1MHz$
Switching Times	t _{on}	_	40		ns	$V_{CC} = 10V, I_C = 500mA$
Ownering Times	t _{off}		500		ns	$I_{B1} = -I_{B2} = 50 \text{mA}$

Notes: 4. Pulse Test: Pulse width \leq 300 μ s. Duty cycle \leq 2.0%.

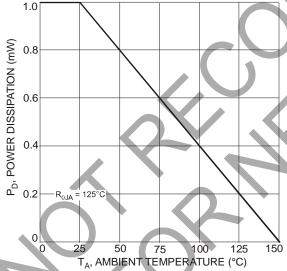


Fig. 1 Max Power Dissipation vs. Ambient Temperature

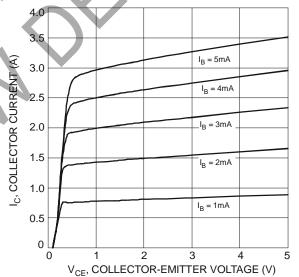


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage



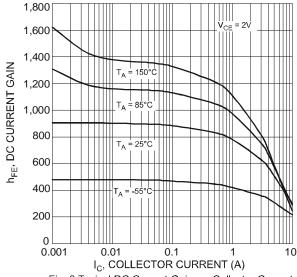


Fig. 3 Typical DC Current Gain vs. Collector Current

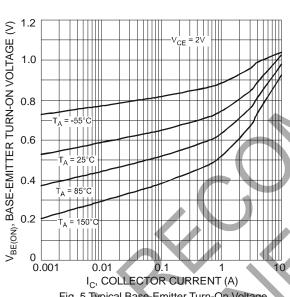


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

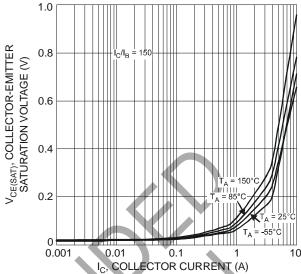


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

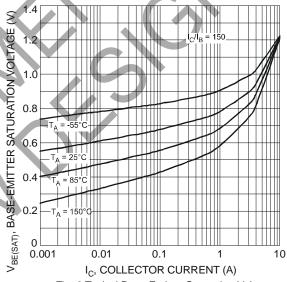


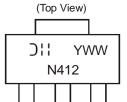
Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

Ordering Information (Note 5)

Device	Packaging	Shipping
DNLS412E-13	SOT-223	2500/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/ap2007.pdf.

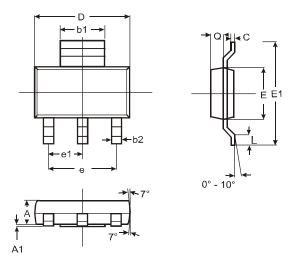
Marking Information



N412 = Product Type Marking Code YWW = Date Code Marking Y = Last digit of year ex: 7 = 2007 WW = Week code 01 - 52

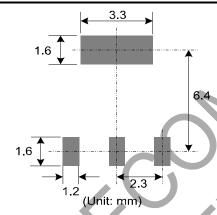


Package Outline Dimensions



SOT-223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b1	2.90	3.10	3.00		
b2	0.60	0.80	0.70		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	_		4.60		
e1	_		2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout:



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